

## 20V Dual P-Channel MOSFET



**SOT-26** 

#### Pin Definition:

1. Gate 1 6. Drain 1 2. Source 2 5. Source 1

3. Gate 2 4. Drain 2



Parameter		Value	Unit	
$V_{DS}$		-20	V	
R <sub>DS(on)</sub> (max)	$V_{GS} = -4.5V$	140		
	$V_{GS} = -2.5V$	200	mΩ	
	V <sub>GS</sub> = -1.8V	300		
$Q_g$		15.23	nC	

#### **Features**

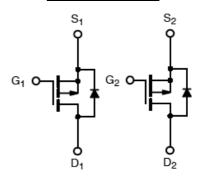
- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

### **Ordering Information**

Part No.	Package	Packing
TSM3911DCX6 RFG	SOT-26	3kpcs / 7" Reel

**Note:** "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

## **Block Diagram**



**Dual P-Channel MOSFET** 

### **Absolute Maximum Ratings** (T<sub>A</sub>=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	-20	V
Gate-Source Voltage		$V_{GS}$	±8	V
Continuous Drain Current		I <sub>D</sub>	-2.2	А
Pulsed Drain Current		I <sub>DM</sub>	-8	А
Continuous Source Current (Diode Co	enduction) (Note 1,2)	I <sub>S</sub>	-0.72	А
Maximum Power Dissipation	T <sub>A</sub> = 25°C	- P <sub>D</sub>	1.15	W
	T <sub>A</sub> =70°C		0.73	
Operating Junction Temperature		T <sub>J</sub>	+150	°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit	
Junction to Case Thermal Resistance	$R\Theta_{JC}$	30	°C/W	
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	80	°C/W	



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**Electrical Specifications** 

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV <sub>DSS</sub>	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-0.45		-0.95	V
Gate Body Leakage	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$	I <sub>DSS</sub>			-1.0	μA
On-State Drain Current	$V_{DS} = -5V, V_{GS} = -5V$	I <sub>D(ON)</sub>	-5			Α
Drain-Source On-State Resistance	$V_{GS} = -4.5V$ , $I_{D} = -2.2A$			115	140	mΩ
	$V_{GS} = -2.5V, I_D = -1.8A$	R <sub>DS(ON)</sub>		163	200	
	$V_{GS} = -1.8V, I_{D} = -1A$			220	300	
Forward Transconductance	$V_{DS} = -5V, I_{D} = -2.2A$	g <sub>fs</sub>		5		S
Diode Forward Voltage	$I_S = -1.05A$ , $V_{GS} = 0V$	V <sub>SD</sub>		- 0.8	-1.2	V
Dynamic (Note 4)						
Total Gate Charge		$Q_g$		15.23		
Gate-Source Charge	$V_{DS} = -6V, I_{D} = -2.8A,$ $V_{GS} = -4.5V$	$Q_gs$		5.49		nC
Gate-Drain Charge		$Q_{gd}$		2.74		
Input Capacitance		C <sub>iss</sub>		882.51		
Output Capacitance	$V_{DS} = -6V$ , $V_{GS} = 0V$ , f = 1.0MHz	C <sub>oss</sub>		145.54		pF
Reverse Transfer Capacitance		C <sub>rss</sub>		97.26		1
Switching (Note 4,5)						
Turn-On Delay Time	$V_{DD} = -6V, R_L = 6\Omega,$ $I_D = -1A, V_{GEN} = -4.5V,$ $R_G = 6\Omega$	t <sub>d(on)</sub>		17.28		
Turn-On Rise Time		t <sub>r</sub>		3.73		
Turn-Off Delay Time		t <sub>d(off)</sub>		36.05		ns
Turn-Off Fall Time		t <sub>f</sub>		6.19		

#### Notes:

- 1. Pulse width limited by the Maximum junction temperature
- 2. Surface Mounted on FR4 Board, t ≤ 5 sec.
- 3. pulse test: PW  $\leq$  300 $\mu$ S, duty cycle  $\leq$  2%
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.

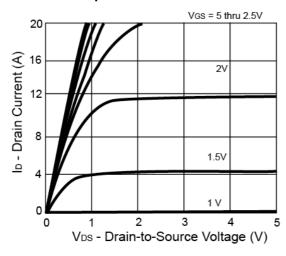


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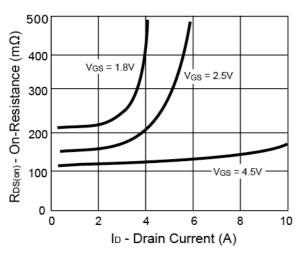


#### **Electrical Characteristics Curves**

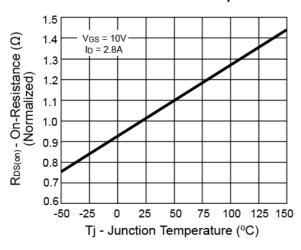
#### **Output Characteristics**



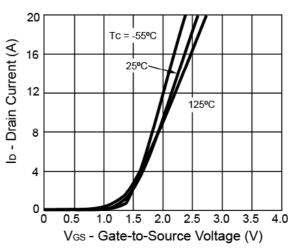
#### **On-Resistance vs. Drain Current**



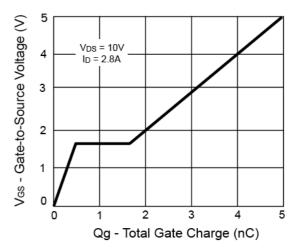
#### **On-Resistance vs. Junction Temperature**



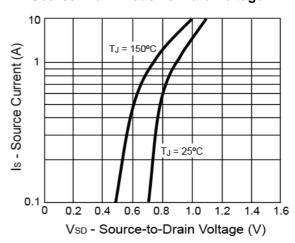
#### **Transfer Characteristics**



#### **Gate Charge**



#### **Source-Drain Diode Forward Voltage**



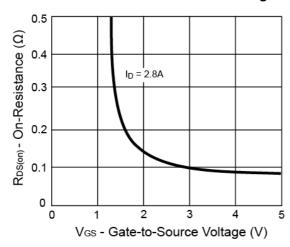


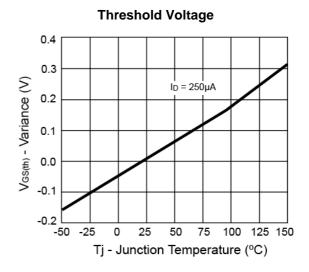
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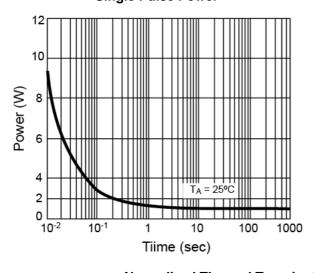
#### **Electrical Characteristics Curves**

#### On-Resistance vs. Gate-Source Voltage

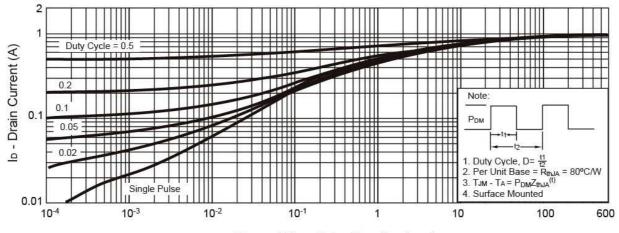




#### **Single Pulse Power**

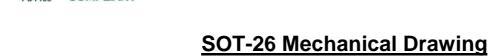


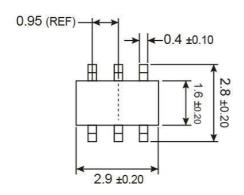
### Normalized Thermal Transient Impedance, Junction-to-Ambient

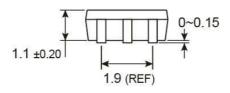


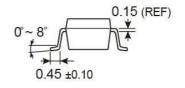
Square Wave Pulse Duration (sec)











Unit: Millimeters

## **Marking Diagram**



1D = Device Code

Y = Year Code

**M** = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr S =May T =Jun U =Jul V =Aug

 $W = Sep \quad X = Oct \quad Y = Nov \quad Z = Dec$ 

L = Lot Code



# TSM3911D 20V Dual P-Channel MOSFET

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